

## ABSTRACT OF THE DISCLOSURE

## ELECTRODE MATERIAL FOR COMPOUND SEMICONDUCTOR

Provided are an electrode material for Group III-V compound semiconductor represented by the general formula  $\text{In}_x\text{Ga}_y\text{Al}_z\text{N}$  (provided that  $x + y + z = 1$ ,  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ , and  $0 \leq z \leq 1$ ) doped with a p-type impurity, capable of obtaining a good ohmic contact, and an electrode using the same, thereby making it possible to reduce a driving voltage of a device using the compound semiconductor.

The electrode material is a metal comprising at least Ca and a noble metal, wherein the total amount of the weight of Ca and the noble metal is not less than 50% by weight and not more than 100% by weight based on the weight of the whole electrode material.

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